

■ Job Information

Subject No.	2020R-47
Job Title	Fixed Term Researcher
Department	Advanced ICT Research Institute / Green ICT Device Advanced Development Center
Work Contents (Research theme)	Research and development on gallium oxide devices (molecular beam epitaxy, device processing and characterization)
Detail of Work Contents	<p>Research and development on fundamental technologies for electrical devices based on novel widegap semiconductor; gallium oxide (Ga₂O₃). The successful candidate will mainly be in charge of Ga₂O₃ thin film growth by molecular beam epitaxy. Additionally, the candidate will work on processing and characterization of Ga₂O₃ devices, too.</p> <p>The Article 15(2) of the Act on the activation of Science and Technology and Innovation will be applied to this work content.</p>
Application requirement	Ph.D. or equivalent in Electrical Engineering or a related discipline, with 5+ years of industry experience (R&D and production). Minimum 3 years of R&D hands-on experiences in molecular beam epitaxy growth of semiconductor thin films. Special consideration will be given to candidates with expertise and experience in molecular beam epitaxy growth on widegap and/or compound semiconductor materials (GaN, SiC, GaAs etc).
Recruiting (Number of people)	1
Period of Employment	hiring date ~ March 31,2021 N.B. Contract will not be renewed..
Salary (basic salary)	¥467,000 ~ ¥510,000/month Basic salary shall be determined by taking into account each employee's experience and task to be engaged in. However, as a basic salary is compliant with government employees' wages, it shall be changed when a basic salary is changed after labor union and the like of NICT agreed under a revision to the government employees' wages.
Work Place	Headquarters (Koganei-shi, Tokyo)
Working frequency	5 days/week

Department name and work place including work contents (research theme) and detail of work contents might change according to organizational change, etc.